

Diffusion equation and spin drag in spin-polarized transport

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We study the role of electron-electron interactions for spin polarized transport using the Boltzmann equation and derive a set of coupled transport equations. For spin polarized transport the electron-electron interactions are important, because they tend to equilibrate the momentum of the two spin species. This “spin drag” effect enhances the resistivity of the system. The enhancement is stronger the lower the dimension and should be measurable in for example a two dimensional electron gas with ferromagnetic contacts. We also include spin flip scattering which has two effects: it equilibrates the spin density imbalance and, provided it has a non s -wave component, also the current imbalance.

I. INTRODUCTION

Recent advances in fabrication of ferromagnetic–semiconductor heterostructures [1] and the observation of spin injection into semiconductors [2] have lead to new interest in transport properties of spin polarized systems. There has been considerable work done in the field of metallic magnetic multilayers, which has been analyzed in terms of transport equations with spin dependent distribution functions [3,4]. These works based their analysis on diffusion transport equations. The justification of using these equations was given by Valet and Fert [5], who derived a spin diffusion equation from the Boltzmann equation in the limit where the spin scattering length is much longer than the momentum relaxation length. Recently, the transport equation were utilized to analyze the feasibility of spin injection into semiconductors with the result that the crucial parameter is the conductivity mismatch between the semiconductor and the ferromagnet [6] and to study theoretically spin-polarized transport in inhomogeneous doped semiconductors [7].

None of these approaches take the electron-electron (e-e) scattering into account. Clearly the e-e interactions play a different role than in usual spin degenerate transport, where the e-e interaction does not provide a mechanism for momentum relaxation and hence has only indirect consequences for transport coefficients. In spin polarized transport the two spin species have different drift velocities and e-e interactions are instrumental in equilibrating this difference. This leads to a spin drag effect where the spins carrying the larger current will drag along the spins carrying the smaller current. This drag effect has been considered recently by D’Amico and Vignale [8,9] in three dimensions using linear response theory. They found that the spin drag resistivity was appreciable and can at elevated temperatures become fractions of the usual resistivity of the metal. In two dimensions the effect of e-e interactions on spin diffusion has been considered theoretically by Takahashi et al. [10,11]. Using a quantum kinetic equation approach, previously utilized in ³He-⁴He solutions [12], they studied the spin diffusion coefficients in two dimensional electron gases. In order to study this spin diffusion they used variational functions but did not include spin relaxation scattering.

In this paper, we use the Boltzmann equation to study spin dependent transport and spin diffusion. We restrict our selves to the study of colinear magnetization and our goal is to derive a set of transport equation in the semiclassical limit. For this purpose the Boltzmann equation is adequate. For the non-colinear case, where phenomena like damped transverse spin modes cannot occur, one must go beyond the present approach, see e.g. [10,11] and references therein. We include impurity scattering, both spin independent and spin flip scattering, as well as e-e scattering. We show that a shifted Fermi–Dirac distribution (SFD), is a valid solution at low temperatures, $T \ll T_F$ and without spin flip scattering. This is also the case for weak e-e scattering, where the problem in absence of spin flip reduces to the ordinary Coulomb drag situation [13,14].

We then go on to discuss the general case at higher temperatures, general interaction strength and finite intrinsic spin flip scattering. Using a SFD ansatz, we find for an isotropic system the following macroscopic transport equations

$$\nabla \cdot \mathbf{J}_s = \left(-\frac{e}{\tau_{sf}^0} \frac{\partial n_s^0}{\partial \mu} \right) (\bar{\mu}_s - \bar{\mu}_{-s}), \quad (1a)$$

$$\nabla \bar{\mu}_s = \frac{e}{\sigma_s} \mathbf{J}_s + \left(\frac{e}{\sigma_D \alpha_s} + \frac{e}{\sigma_{sf,s}} \right) (\mathbf{J}_s - \alpha_s \mathbf{J}_{-s}). \quad (1b)$$

Here J_s is the current carried by electrons with spin s , $\bar{\mu}_s$ is the local spin dependent electro chemical potential, σ_s is the conductivity of the spin s electron gas, τ_{sf}^0 is a spin lifetime due to intrinsic spin flip processes, $\sigma_{\text{sf},s}$ is a spin current conversion conductivity arising from the angle dependence of spin flip scattering, and $\alpha_s = n_s^0/n_{-s}^0$ is the relative spin density, see Eqs. (35),(39) for definitions. Finally σ_D is the spin drag conductivity given by

$$(\sigma_D)^{-1} = \frac{\hbar^2}{de^2 n_s n_{-s}} \int \frac{d\mathbf{q}}{(2\pi)^d} \int_0^\infty d\omega q^2 |e\phi(q)|^2 \frac{\text{Im}\chi_s(q, \omega) \text{Im}\chi_{-s}(q, \omega)}{k_B T \sinh^2(\hbar\omega/2k_B T)}, \quad (2)$$

where $\text{Im}\chi_s$ is the polarization function

$$\text{Im}\chi_s(q, \omega) = \pi \int \frac{d\mathbf{k}}{(2\pi)^d} [f_s^0(|\mathbf{k} + \mathbf{q}|) - f_s^0(k)] \delta(\varepsilon_{|\mathbf{k} + \mathbf{q}|s} - \varepsilon_{ks} - \hbar\omega). \quad (3)$$

The formula (2) is well-known from Coulomb drag [13]. At low temperatures it goes $(\sigma_D)^{-1} \propto T^2$ in two and three dimensions, while in one dimension it is proportional to T , see e.g. [15].

The first transport equation (1a) is the continuity equation, which expresses the conservation of current in the presence of spin flip processes. The second equation (1b) is a generalized Ohm's law. The first term on the right hand side is the usual Ohm's law, while the second term describes that a momentum imbalance between the two spin directions gives rise to an additional resistance if there is a mechanism for conversion of spin current. There are two such processes possible. This first one is the spin drag effect mentioned above, where e-e scattering makes transfer of momentum possible. The second one is due elastic spin flip scattering on for example magnetic impurities, which can convert a current with one spin polarization to a current of the opposite polarization, if the spin flip matrix element has an angular dependence. For example if the spin flip predominately scatters forward it means that a spin flip scattering is accompanied with a transfer of momentum. In contrast if the spin flip scattering is purely s -wave scattering the momentum transfer between the spin channels is on average equal to zero. This can be seen mathematically from the expression for τ_{sf} in Eq. (35c). The derivation of the these two terms is the main result of the present paper.

Two consequences of the spin current relaxation terms can immediately be read off. Firstly, they give rise to an increased resistivity in the case where the current is spin polarized. For example, taking $J_\downarrow = 0$ the effective resistivity for electrons with spin $\uparrow$ becomes $(1/\sigma_\uparrow + 1/\sigma_D\alpha_s + 1/\sigma_{\text{sf},s})^{-1}$ and hence an enhanced resistivity. Secondly, from Eqs. (1) we get a diffusion equation for the electro chemical potential difference

$$\nabla^2(\bar{\mu}_s - \bar{\mu}_{-s}) = \frac{\bar{\mu}_s - \bar{\mu}_{-s}}{\ell_{\text{sf}}^2}, \quad (4)$$

where

$$\frac{1}{\ell_{\text{sf}}^2} = \left[-\frac{e^2}{\tau_{\text{sf}}^0} \frac{\partial n_s^0}{\partial \mu} \right] \sum_s \left[\frac{1}{\sigma_s} + \left(\frac{1}{\sigma_{\text{sf},s}} + \frac{1}{\sigma_D\alpha_s} \right) (1 + \alpha_s) \right]. \quad (5)$$

This shows that the intrinsic spin relaxation length is decreased by the spin drag and angle dependent spin flip effects.

Similarly, we get that the following weighted sum of electro chemical potentials must vanish,

$$\nabla^2(c_{-s}\bar{\mu}_s + c_s\bar{\mu}_{-s}) = 0, \quad (6)$$

where

$$c_s = \frac{\partial n_s^0}{\partial \mu} \frac{1}{\sigma_s} + \left(\frac{1}{\sigma_{\text{sf},s}} + \frac{1}{\sigma_D\alpha_s} \right) \left(\frac{\partial n_s^0}{\partial \mu} + \alpha_s \frac{\partial n_{-s}^0}{\partial \mu} \right). \quad (7)$$

Below we derive Eqs. (1a),(1b) and estimate the spin drag contributions. For the two-dimensional case, we have also performed the integration of Eq. (2) numerically.

II. BOLTZMANN EQUATION FOR COLINEAR SPIN TRANSPORT

We base our analysis on the Boltzmann equation for transport through a system with lifted spin degeneracy. We take the current to run in the x -direction and denote the non-equilibrium distribution function $f_s(\mathbf{k})$ and the equilibrium Fermi-Dirac distribution function f_0

$$f_0(\varepsilon_{ks}) = \frac{1}{e^{\beta(\varepsilon_{ks} - \mu_0)} + 1}, \quad (8)$$

where μ_0 is the chemical potential and β as usual the inverse temperature. The eigenenergies are denoted ε_{ks} , where s is the spin quantum number and $\mathbf{k}$ the quantum number labeling the relevant states crossing the Fermi level. For simplicity we assume a parabolic dispersion and we write

$$\varepsilon_{ks} = \frac{\hbar^2 k^2}{2m} + \varepsilon_s^0, \quad (9)$$

where ε_s is the band off-set which can be spin dependent if the material is ferromagnetic.

The linearized Boltzmann equation then reads

$$v_x(\mathbf{k}) \frac{\partial f_s(\mathbf{k}, x)}{\partial x} - \frac{eE_x}{\hbar} \frac{\partial f_0(\varepsilon_{ks})}{\partial k_x} = \left(\frac{\partial f_s(\mathbf{k}, x)}{\partial t} \right)_{\text{coll.}}. \quad (10)$$

We take the collision integral to include elastic scattering and e-e scattering

$$\left(\frac{\partial f_s(\mathbf{k})}{\partial t} \right)_{\text{coll.}} = H_0[f_s](\mathbf{k}) + H_{\text{sf}}[f_s, f_{-s}](\mathbf{k}) + H_{e-e}[f_s, f_s](\mathbf{k}) + H_{e-e}[f_s, f_{-s}](\mathbf{k}), \quad (11)$$

where H_0 is the scattering from impurities (or quasielastic phonon scattering) giving rise to a momentum relaxation

$$H_0[f_s](\mathbf{k}) = - \int \frac{d\mathbf{k}'}{(2\pi)^d} W_s^0(\mathbf{k}, \mathbf{k}') [f_s(\mathbf{k}) - f_s(\mathbf{k}')] \delta(\varepsilon_{ks} - \varepsilon_{k's}), \quad (12)$$

and where H_{sf} describes elastic scattering processes that flip the spin

$$H_{\text{sf}}[f_s, f_{-s}](\mathbf{k}) = - \int \frac{d\mathbf{k}'}{(2\pi)^d} W_{sf}(\mathbf{k}, \mathbf{k}') [f_s(\mathbf{k}) - f_{-s}(\mathbf{k}')] \delta(\varepsilon_{ks} - \varepsilon_{k'-s}). \quad (13)$$

Finally, the e-e scattering is after the linearization given by [16]

$$\begin{aligned} H_{e-e}[f_s, f_{s'}](\mathbf{k}) = & -\frac{2\pi}{\hbar k T} \int \frac{d\mathbf{k}'}{(2\pi)^d} \int \frac{d\mathbf{q}}{(2\pi)^d} |U_{ss'}(\mathbf{q}, \varepsilon_{\mathbf{k}} - \varepsilon_{\mathbf{k}+\mathbf{q}})|^2 \\ & \times \delta(\varepsilon_{\mathbf{k}} + \varepsilon_{\mathbf{k}'} - \varepsilon_{\mathbf{k}+\mathbf{q}} - \varepsilon_{\mathbf{k}'-\mathbf{q}}) \\ & \times f_0(\varepsilon_{ks}) f_0(\varepsilon_{k's'}) [1 - f_0(\varepsilon_{|\mathbf{k}+\mathbf{q}|s})] [1 - f_0(\varepsilon_{|\mathbf{k}'-\mathbf{q}|s'})] \\ & \times [\Psi_s(\mathbf{k}) + \Psi_{s'}(\mathbf{k}') - \Psi_s(\mathbf{k} + \mathbf{q}) - \Psi_{s'}(\mathbf{k}' - \mathbf{q})], \end{aligned} \quad (14)$$

where the deviation from equilibrium is expressed in the function Ψ through

$$f_s(\mathbf{r}, \mathbf{k}) = f_s^0(k) + \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \Psi_s(\mathbf{r}, \mathbf{k}). \quad (15)$$

The interaction $U_{ss'}$ is the Coulomb interaction between two electrons with spin s and s' . It can in principle depend on the relative direction of the spin if exchange is included. This set of integral equations cannot be solved in general and one must either solve them numerically (for example as in Ref. [17]) or proceed with approximate methods.

One simplification is however possible from symmetry. Because of the cylindrical symmetry the functions $\Psi_s(\mathbf{k})$ only depend on the angle between $\mathbf{k}$ and the direction of the current, which we here choose to be in the x -direction. Denoting this angle by θ we have $\cos \theta = \mathbf{k} \cdot \hat{\mathbf{x}}/k$ and we can write

$$\Psi_s(\mathbf{r}, \mathbf{k}) = \Psi_s(x, k, \theta). \quad (16)$$

It is convenient to expand the distribution function in harmonics of the angle θ as

$$\Psi_s(x, k, \theta) = \sum_{n=0}^{\infty} g_s^{(n)}(x, k) \cos n\theta, \quad (17)$$

which we utilize in the next section.

III. SPIN DRAG WITHOUT SPIN FLIP PROCESSES FOR $T \ll T_F$

In this section we study the Boltzmann equation in the presence of e-e interaction, but in the absence of spin flip processes, i.e. $H_{sf} = 0$. Furthermore, because a low temperature expansion allows for a solution of the Boltzmann equation, we start by examining this limit and later we discuss the validity of this solution even at elevated temperatures. It turns out that the solution in the low temperature regime corresponds to a SFD distribution.

In the low temperature limit we see from Eq. (10) that the second term on the left hand side (the driving term) restricts $\varepsilon_{\mathbf{k}s}$ to lie close to the Fermi level, such that the deviation $\Psi_s(\mathbf{k})$ need only be evaluate at k_F . This is therefore also true for the distribution function in the elastic collision term, H_0 . Due to the Pauli principle this will also be the case for the Ψ_s 's in the e-e collision integrals, which is seen as follows. Using standard tricks (see e.g. [13]), we rewrite the e-e collision term as

$$\begin{aligned} H_{e-e}[f_s, f_{s'}](\mathbf{k}) = & -\frac{2\pi}{\hbar} \int_{-\infty}^{\infty} \frac{d\omega}{2\pi} \int \frac{d\mathbf{k}'}{(2\pi)^d} \int \frac{d\mathbf{q}}{(2\pi)^d} |U_{ss'}(\mathbf{q}, \varepsilon_k - \varepsilon_{|\mathbf{k}+\mathbf{q}|s})|^2 \\ & \times \frac{1}{kT \sinh^2(\hbar\omega/k_B T)} \text{Im} \chi_s(\mathbf{k}, \mathbf{q}; \omega) \text{Im} \chi_{s'}(\mathbf{k}', -\mathbf{q}; \omega) \\ & \times [\Psi_s(\mathbf{k}) + \Psi_{s'}(\mathbf{k}') - \Psi_s(\mathbf{k} + \mathbf{q}) - \Psi_{s'}(\mathbf{k}' - \mathbf{q})], \end{aligned} \quad (18)$$

where

$$\text{Im} \chi_s(\mathbf{k}, \mathbf{q}; \omega) = \pi [f_0(\varepsilon_{|\mathbf{k}+\mathbf{q}|s}) - f_0(\varepsilon_{ks})] \delta(\varepsilon_{|\mathbf{k}+\mathbf{q}|s} - \varepsilon_{ks} - \hbar\omega). \quad (19)$$

Now, at low temperatures the factor $1/\sinh^2$ restricts the ω -integral to small ω of order kT , and hence $\varepsilon_{|\mathbf{k}+\mathbf{q}|s}$ in (19) deviates from ε_{ks} by an amount of order kT and we expand $\text{Im} \chi_s$ as

$$\text{Im} \chi_s(\mathbf{k}, \mathbf{q}; \omega) \approx \pi \hbar \omega \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \delta(\varepsilon_{|\mathbf{k}+\mathbf{q}|s} - \varepsilon_{ks} - \hbar\omega). \quad (20)$$

From this we conclude that both ε_{ks} and $\varepsilon_{k's'}$ (and hence also $\varepsilon_{|\mathbf{k}+\mathbf{q}|s}$ and $\varepsilon_{|\mathbf{k}'-\mathbf{q}|s'}$) are within a shell of order $k_B T$ from the Fermi level. To leading order in kT/ε_F we can therefore neglect the dependence on k and keep only the angular dependence of Ψ_s . Therefore in the following we replace

$$\Psi_s(\mathbf{k}) \approx \Psi_s(k_{Fs}, \theta), \quad (21)$$

where k_{Fs} is the Fermi wave vector for the spin direction s .

Now we expand the function Ψ in harmonics of the angle θ as in Eq. (17). Inserting (15) and (17) into the Boltzmann equation gives for the left hand side

$$\frac{\hbar k_{sx}}{m} \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \left(\frac{\partial \Psi_s}{\partial x} - eE_x \right) = \sum_n \frac{\hbar k_s \cos \theta}{m} \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \left(\cos n\theta \frac{\partial g_s^{(n)}}{\partial x} - \frac{eE}{\hbar} \right) \quad (22)$$

and for the right hand side we have two terms. The first one is the spin conserving impurity scattering term which becomes

$$H_0[f_s] = - \sum_n \cos(n\theta) g_s^{(n)} \frac{1}{\tau_{tr}^n} \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right), \quad (23)$$

where we defined the transport times of order n

$$\frac{1}{\tau_{tr,s}^n} = \int \frac{d\mathbf{k}'}{(2\pi)^d} W_s^0(\mathbf{k}, \mathbf{k}') [1 - \cos n\theta_{\mathbf{k}\mathbf{k}'}] \delta(\varepsilon_{ks} - \varepsilon_{k's}), \quad (24)$$

and where $\theta_{\mathbf{k}\mathbf{k}'}$ is the angle between $\mathbf{k}$ and $\mathbf{k}'$. The second term is the one with the e-e scattering. When the expansion (17) is inserted into the e-e interaction terms different n do not couple, see for example the derivation in Ref. [17]. The trick is to write for example the angle of $\mathbf{k}' - \mathbf{q}$ as $\cos n\theta_{\mathbf{k}'-\mathbf{q},\mathbf{x}} = \cos n(\theta_{\mathbf{k}'-\mathbf{q},\mathbf{k}} + \theta_{\mathbf{k},\mathbf{x}}) = \cos n\theta_{\mathbf{k}'-\mathbf{q},\mathbf{k}} \cos n\theta_{\mathbf{k},\mathbf{x}} - \sin n\theta_{\mathbf{k}'-\mathbf{q},\mathbf{k}} \sin n\theta_{\mathbf{k},\mathbf{x}}$ and note that the sin terms vanish due to symmetry. Therefore we can express the e-e collision term as

$$H_{e-e}[f_s, f_{s'}](k, \theta) = \sum_n \cos(n\theta) \left(g_s^{(n)} J^{(n)} + g_{s'}^{(n)} I^{(n)} \right), \quad (25)$$

where $J^{(n)}$ corresponds to the first and third term in Eq. (18) while $I^{(n)}$ corresponds to the second and fourth term.

Now a set of equations for the coefficients $g_s^{(n)}$ can be extracted by multiplying the Boltzmann equation with $\cos n'\theta$ and integrating over θ , while using that $\int d\theta \cos n\theta \cos n'\theta \propto \delta_{nn'}$. The left hand side of Eq. (22) is expanded in harmonics using that $\cos \theta \cos n\theta = \frac{1}{2} [\cos \theta(n+1) + \cos \theta(n-1)]$. We find the following set of equations

$$\frac{\partial g_s^{(1)}}{\partial x} = 0, \quad (26a)$$

$$\frac{\hbar k}{2m} \frac{\partial}{\partial x} \left(g_s^{(0)} + \frac{g_s^{(2)}}{2} + e\phi \right) \eta_s = \left(g_s^{(1)} \frac{\eta_s}{\tau_{\text{tr}}^1} + g_s^{(1)} (J^{(1)} + I^{(1)}) + g_{-s}^{(1)} I^{(1)} \right), \quad (26b)$$

$$\frac{1}{2} \frac{\hbar k}{2m} \frac{\partial}{\partial x} \left(g_s^{(n-1)} + g_s^{(n+1)} \right) \eta_s = \left(g_s^{(n)} \frac{\eta_s}{\tau_{\text{tr}}^n} + g_s^{(n)} (J^{(n)} + I^{(n)}) + g_{-s}^{(n)} I^{(n)} \right), \quad n \geq 2 \quad (26c)$$

where

$$\eta_s = \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right). \quad (27)$$

The solution of these equation is that $g_s^{(n)} = 0$ for $n \geq 2$. This is due to the fact that $\partial_x g_s^{(1)} = 0$ which decouples the equations for $n \geq 2$ from the two first. Eq. (26a) expresses current conservation within each spin species. If we include spin flip scattering in the equation, then the equations couple because $\partial_x g_s^{(1)} \neq 0$.

Now we note that setting $g_s^{(n)} = 0$ for $n \geq 2$ corresponds precisely to a linearized shifted Fermi-Dirac (SFD) distribution

$$f_s^{\text{SFD}}(k) = f_0(\varepsilon_s(\mathbf{k} + \delta\mathbf{k}_s) - \delta\mu_s), \quad (28)$$

from which we read off (for $\delta\mathbf{k}$ in the x -direction),

$$g_s^{(0)} = \delta\mu_s, \quad g_s^{(1)} \cos \theta = \hbar v_x \delta k_s \Rightarrow g_s^{(1)} = -\frac{\hbar^2 k_{Fs}}{m} \delta k_s. \quad (29)$$

From Eqs. (26), one can now determine g_s^0 and g_s^1 . They correspond to the change of the local charge densities and to the local currents, respectively. This we will see in the next section, where we use the SFD ansatz to study the general case.

IV. MACROSCOPIC TRANSPORT EQUATIONS

Above we saw that at low temperature the exact solution of the Boltzmann equation in absence of spin flip was a shifted Fermi-Dirac function. The same conclusion applies to the situation of arbitrary temperatures but weak e-e scattering, because this limit corresponds to the usual Coulomb drag regime. This is however no longer necessarily true at arbitrary e-e scattering, when the temperature increases, or when spin flip processes are included. Nevertheless, we shall assume in the following that the SFD distribution is a good approximation for the exact distribution function. The argument for doing this is as follows: the e-e interactions will drag the distribution functions towards shifted Fermi-Dirac distributions because the inter spin channel e-e collision terms vanish for $f_s = f_s^{\text{SFD}}$, i.e. $H_{e-e}[f_s^{\text{SFD}}, f_s^{\text{SFD}}] = 0$. Since the e-e scattering rate increases as $\tau_{e-e}^{-1} \approx (\varepsilon_F/\hbar)(kT/\varepsilon_F)^2$, increasing the temperature actually helps. Furthermore, since the energy dependence of the elastic scattering is important in determining the actual shape of the distribution functions, and because we do not want to into details of this sort, we will use view the SFD distribution functions as reasonable parameterizations of the true distribution function.

Our starting point is thus an ansatz distribution function given by

$$f_s(k) = f_0(\varepsilon_{ks}) + \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \delta\mu_s(x) - \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \hbar v_x \delta k_s(x). \quad (30)$$

Here $\delta\mu_s$ corresponds to a change of the local chemical potential and hence also to the local density, while δk_s describes a shift of the distribution function in $\mathbf{k}$ -space and thus gives a finite drift velocity. Inserting this into the Boltzmann equation gives for the left hand side

$$\text{LHS} = v_x \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \left(\frac{\partial}{\partial x} (\delta \mu_s - \hbar v_x \delta k_s) - e E_x \right), \quad (31)$$

and for the right hand side we have three terms. The spin conserving collision term becomes

$$H_0[f_s] = -\hbar v_x \delta k_s \frac{1}{\tau_{\text{tr},s}} \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right), \quad (32)$$

where the usual transport time is

$$\frac{1}{\tau_{\text{tr},s}} = \int \frac{d\mathbf{k}'}{(2\pi)^d} W_s^0(\mathbf{k}, \mathbf{k}') [1 - \cos \theta_{\mathbf{k}\mathbf{k}'}] \delta(\varepsilon_{ks} - \varepsilon_{k's}). \quad (33)$$

The second term on the right hand side is the spin flip scattering term which becomes

$$H_{\text{sf}}[f_s, f_{-s}] = \left(\hbar v_x \delta k_s \frac{1}{\tau_{\text{sf},\text{tr}}} - (\delta \mu_s - \delta \mu_{-s}) \frac{1}{\tau_{\text{sf}}^0} - \hbar v_x (\delta k_s - \delta k_{-s}) \frac{1}{\tau_{\text{sf}}} \right) \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right), \quad (34)$$

where the three different spin flip scattering times are given by

$$\frac{1}{\tau_{\text{sf}}^0} = \int \frac{d\mathbf{k}'}{(2\pi)^d} W_{\text{sf}}(\mathbf{k}, \mathbf{k}') \delta(\varepsilon_{ks} - \varepsilon_{k'-s}), \quad (35a)$$

$$\frac{1}{\tau_{\text{sf},\text{tr}}} = \int \frac{d\mathbf{k}'}{(2\pi)^d} W_{\text{sf}}(\mathbf{k}, \mathbf{k}') [1 - \cos \theta_{\mathbf{k}\mathbf{k}'}] \delta(\varepsilon_{ks} - \varepsilon_{k'-s}), \quad (35b)$$

$$\frac{1}{\tau_{\text{sf}}} = \int \frac{d\mathbf{k}'}{(2\pi)^d} W_{\text{sf}}(\mathbf{k}, \mathbf{k}') \cos \theta_{\mathbf{k}\mathbf{k}'} \delta(\varepsilon_{ks} - \varepsilon_{k'-s}). \quad (35c)$$

Finally, the e-e scattering is given by $\sum_{s'} H_{e-e}[f_s, f_{s'}]$. But in accordance with detailed balance the e-e scattering between two identical Fermi-Dirac distributions is zero, $H_{e-e}[f_s, f_s] = 0$, and we are left with

$$\begin{aligned} H_{e-e}[f_s, f_{-s}] &= -\frac{\hbar^2}{m} \int_{-\infty}^{\infty} \frac{d\omega}{2\pi} \int \frac{d\mathbf{k}'}{(2\pi)^d} \int \frac{d\mathbf{q}}{(2\pi)^d} |U_{s,-s}(\mathbf{q}, \varepsilon_k - \varepsilon_{|\mathbf{k}+\mathbf{q}|})|^2 \\ &\quad \times \frac{1}{kT \sinh^2(\hbar\omega/k_B T)} \text{Im} \chi_s(\mathbf{k}, \mathbf{q}; \omega) \text{Im} \chi_{-s}(\mathbf{k}', -\mathbf{q}; \omega) \\ &\quad \times q_x [\delta k_s - \delta k_{-s}]. \end{aligned} \quad (36)$$

The final form of the Boltzmann equation is thus

$$(31) = (32) + (34) + (36). \quad (37)$$

Next we find the current and the density. They are given by

$$\begin{aligned} J_s &\equiv -e \int \frac{d\mathbf{k}}{(2\pi)^d} v_x f_s(\mathbf{k}) \\ &= e \int \frac{d\mathbf{k}}{(2\pi)^d} \hbar v_x^2 \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \delta k_s = \frac{\hbar e}{m} n_s^0 \delta k_s, \end{aligned} \quad (38a)$$

$$\begin{aligned} \delta \rho_s &\equiv -e \int \frac{d\mathbf{k}}{(2\pi)^d} [f_s(\mathbf{k}) - f_s^0(\mathbf{k})] \\ &= -e \int \frac{d\mathbf{k}}{(2\pi)^d} \left(-\frac{\partial f_0(\varepsilon_{ks})}{\partial \varepsilon_{ks}} \right) \delta \mu_s = -e \frac{\partial n_s^0}{\partial \mu} \delta \mu_s. \end{aligned} \quad (38b)$$

where is the density of states. We find two transport equations for current and charge density or chemical potentials by integrating (37) and also (37) multiplied by v_x with respect to $\mathbf{k}$, and we arrive at Eq. (1), where

$$\alpha_s = \frac{n_s^0}{n_{-s}^0}, \quad (39a)$$

$$\sigma_s = \frac{n_s^0 e^2}{m} e \left(\frac{1}{\tau_{\text{tr},s}} + \frac{1}{\tau_{\text{sf},\text{tr}}} \right)^{-1}, \quad (39b)$$

$$\sigma_{\text{sf},s} = \frac{n_s^0 e^2 \tau_{\text{sf}}}{m}. \quad (39c)$$

In (1a) we have introduced the drag conductivity defined in Eq. (2). In deriving the drag term, we have made use of the result obtained for usual Coulomb drag in e.g. Ref. ([13]). Furthermore, the local electro chemical potential has been defined as

$$\bar{\mu}_s = \mu_s + e\phi, \quad (40)$$

where ϕ is the electrical potential.

V. EVALUATION OF THE SPIN DRAG RESISTIVITY

A. One dimension

The polarization function is in one dimension at small temperatures, where we can perform an ω -expansion, given by

$$\text{Im}\chi_s(q, \omega) \approx \omega \frac{m^2}{4\hbar^3 q^2} \left(-\frac{\partial f_0(\varepsilon_{q/2,s})}{\partial \varepsilon_{q/2,s}} \right). \quad (41)$$

Inserting this into the formula for σ_D^{-1} , performing the ω -integration for the case of a non-magnetic conductor, $\varepsilon_{ks} = \varepsilon_k$, and using that $[f'_0(\varepsilon)]^2 \simeq (6kT)^{-1} \delta(\varepsilon - \varepsilon_F)$, we find

$$\sigma_D^{-1} \approx \frac{kT}{\varepsilon_F} \frac{\pi^2 k_F^3}{64} \frac{\hbar}{e^2} \frac{|U(2k_F)|^2}{\varepsilon_F^2}. \quad (42)$$

The spin-drag resistance is thus proportional to temperature and dependent on the Coulomb backscattering matrix element. Clearly, this contribution can be very large at finite temperatures. However, in strictly one dimensions, where Fermi liquid theory is not expected to apply, the Boltzmann equation is not a correct starting point and one should be somewhat careful about drawing firm conclusions from this. Nevertheless, this Fermi's Golden rule result is indicative of e-e interactions being very important for spin transport in one dimension.

B. Two dimensions

For the two dimensional case we start by deriving a low temperature result and go on to compare it with a full numerical integration of σ_D^{-1} . At small ω and q the imaginary part of the polarization function is given by

$$\text{Im}\chi_s(q, \omega) \approx \omega \frac{m^2}{2\pi\hbar^3 q^3 k_F}, \quad (43)$$

and the screened static Coulomb interaction is

$$U(q) = \frac{e^2}{2\pi\varepsilon_0\varepsilon_r} \frac{1}{(q + q_{TF})}. \quad (44)$$

In this approximation, the $\mathbf{q}$ -integral becomes

$$\int dq q^3 \frac{1}{(q + q_{TF})^2}, \quad (45)$$

which is clearly not convergent and therefore we set the upper limit to be $2k_F$, because $\text{Im}\chi$ is zero for momentum exchange larger than $2k_F$. With these inputs, we arrive at the following approximate expression

$$\sigma_D^{-1} \approx \left(\frac{kT}{\varepsilon_F} \right)^2 \frac{\hbar}{e^2} \frac{\pi^2}{3} \frac{(1 + \gamma) \ln(1 + \gamma) - \gamma}{\gamma^2 (1 + \gamma)}, \quad (46)$$

where $\gamma = 2k_F/q_{TF}$ and $q_{TF} = me^2/2\pi\varepsilon_0\varepsilon_r\hbar^2$ is the two dimensional inverse Thomas-Fermi screening length. Typically γ is of order 1. This means that spin drag resistivity can be equal to a fraction of the quantum resistance and should therefore indeed be measurable for standard high mobility quantum wells.

We have also integrated the spin drag formula numerically, see Ref. [14] for details. The result is shown in Fig. 1 for realistic numbers for a two dimensional GaAs electron gas. The integration is done using the full dynamically screened interaction for a quantum well with finite thickness. The approximate formula (46) is seen to overestimate the spin drag effect slightly.

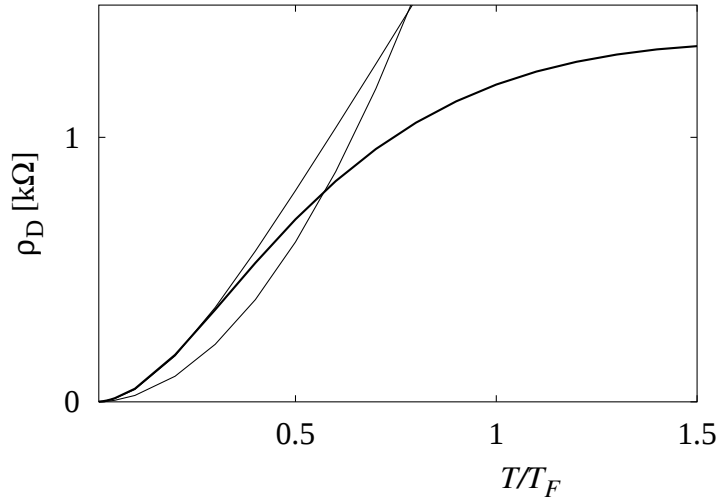


FIG. 1. The spin-drag resistivity in the two-dimensional case as a function of temperature. The full line is the numerical integration of Eq. (2) for a two-dimensional quantum well of thickness 10 nm, electron density $2 \times 10^{15} \text{ m}^{-2}$. We have used typical parameters for GasAs based heterostructures. The right most thin line is the approximate expression in Eq. (46), while the left thin line is the result of a integrating Eq. (2), but using the $T = 0$ expression for $\chi(q, \omega)$.

VI. CONCLUSIONS

We have derived a set of transport equations for spin polarized drag which incorporate e-e scattering. This has been done within the framework of the Boltzmann equation. First we showed that in the absence of spin-flip scattering and at low temperatures the exact solution of the Boltzmann equation corresponds to two shifted Fermi-Dirac distribution functions. Furthermore, if the interaction is weak one can use perturbation theory and arrive at the same conclusion following the lines of argument from usual Coulomb drag. Having observed that the shifted Fermi-Dirac distribution is correct at low temperatures or weak e-e scattering, we go on to the general case which is solved approximately by using the SFD as an ansatz, which allows for a solution of coupled Boltzmann equations.

The main conclusion from this is that e-e interaction introduces a spin drag term, which tends to drag the spin currents to be equal. There are two such mechanisms namely e-e interactions, which is temperature dependent, and angular dependent elastic spin flip scattering, which is temperature independent. Therefore if a spin polarized current is driven through the system, the spin drag will give rise to an additional resistivity. This resistivity increases with temperature. We have solved for the spin drag resistivity numerically in two dimensions which shows that it can become considerable and even exceed the ordinary impurity scattering induced resistivity. The spin drag should thus be measurable in for example a structure combining a two dimensional electron gas with ferromagnetic materials or for one-dimensional systems e.g. made by nanotechnology in semiconductors or by contacting nanotubes to ferromagnetic contacts.

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